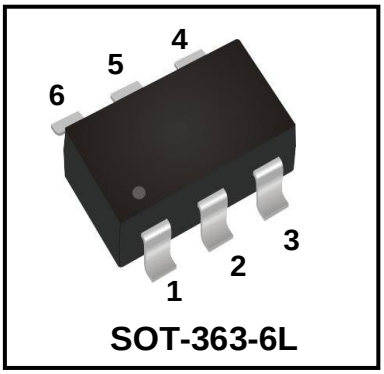
WT856BDW

Dual PNP Transistor



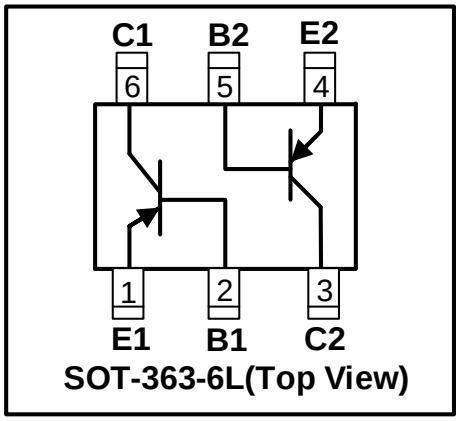
Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

Mechanical Characteristics

- SOT-363-6L Package
- Marking : Making Code
- RoHS Compliant & HF

Schematic & PIN Configuration



\ Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	-80	V
Collector Emitter Voltage	V_{CEO}	-65	V
Emitter Base Voltage	V_{EBO}	-5	V
Collector Current−Continuous	I_C	-0.1	A
Power Dissipation	P_D	300	mW
Junction Temperature	T_j	-55 ~ 150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	328	°C/W

Electrical Characteristics (T_{amb}=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -10μA, I_E = 0	-80	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -10mA, I_B = 0	-65	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -1μA, I_C = 0	-5	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB} = -30V, I_E = 0	-	-	-15	nA
DC Current Gain	h_{FE}	V_{CE} = -5V, I_C = -2mA	220	-	475	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -10mA, I_B = -0.5mA	-	-	-0.3	V
		I_C = -100mA, I_B = -5mA	-	-	-0.65	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = -10mA, I_B = -0.5mA	-	-0.7	-	V
		I_C = -100mA, I_B = -5mA	-	-0.9	-	
Base-Emitter Voltage	$V_{BE(on)}$	V_{CE} = -5V, I_C = -2mA	-	-	-0.75	V
		V_{CE} = -5V, I_C = -10mA	-	-	-0.82	
Transition Frequency	f_T	V_{CE}= -5V,I_C= -10mA,f=100MHz	100	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}= -10V,f=1MHz	-	-	4.5	pF

Typical Characteristics

Figure 1.Static Characteristics

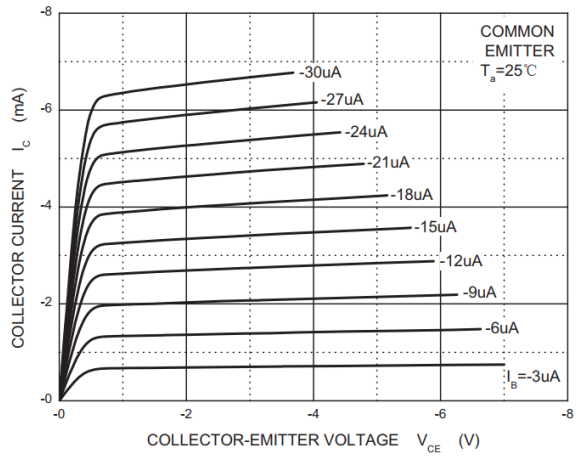


Figure 2. h_{FE} vs. I_C

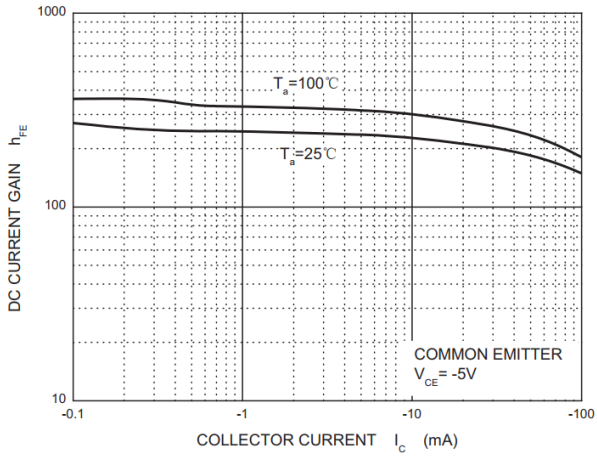


Figure 3. $V_{CE(sat)}$ vs. I_C

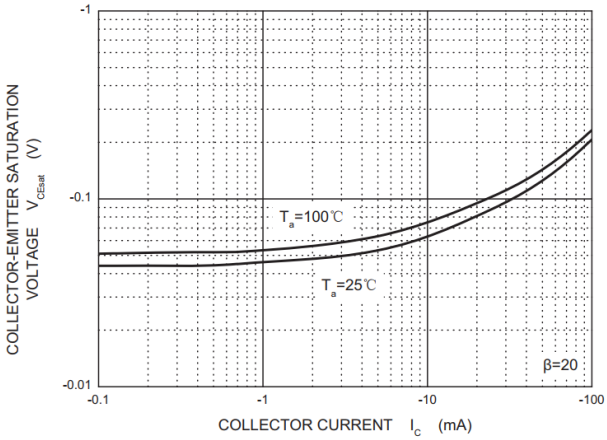


Figure 4. $V_{BE(sat)}$ vs. I_C

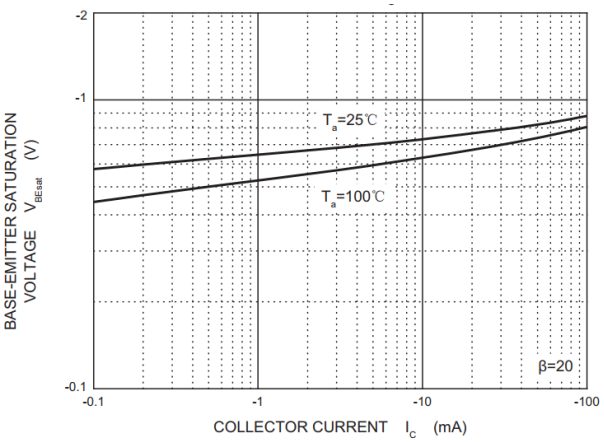


Figure 5. I_C vs. V_{BE}

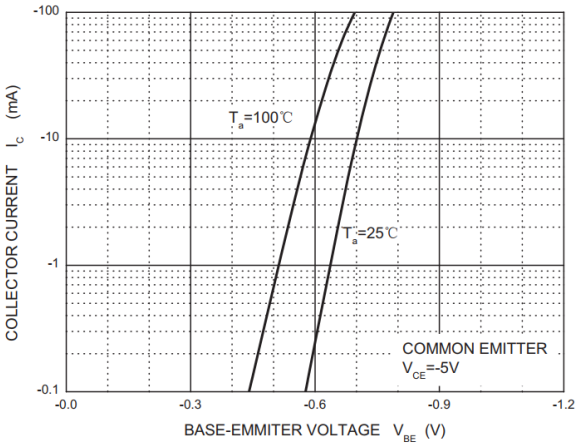
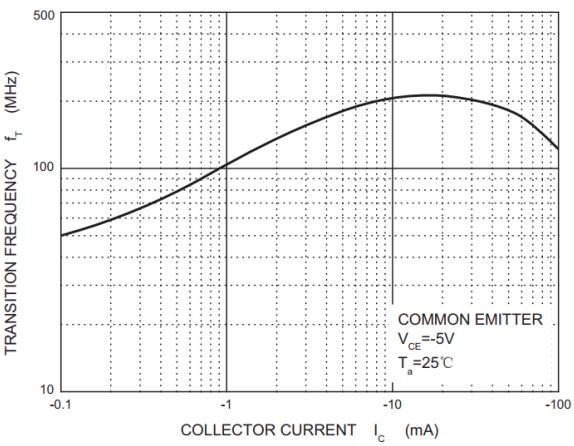
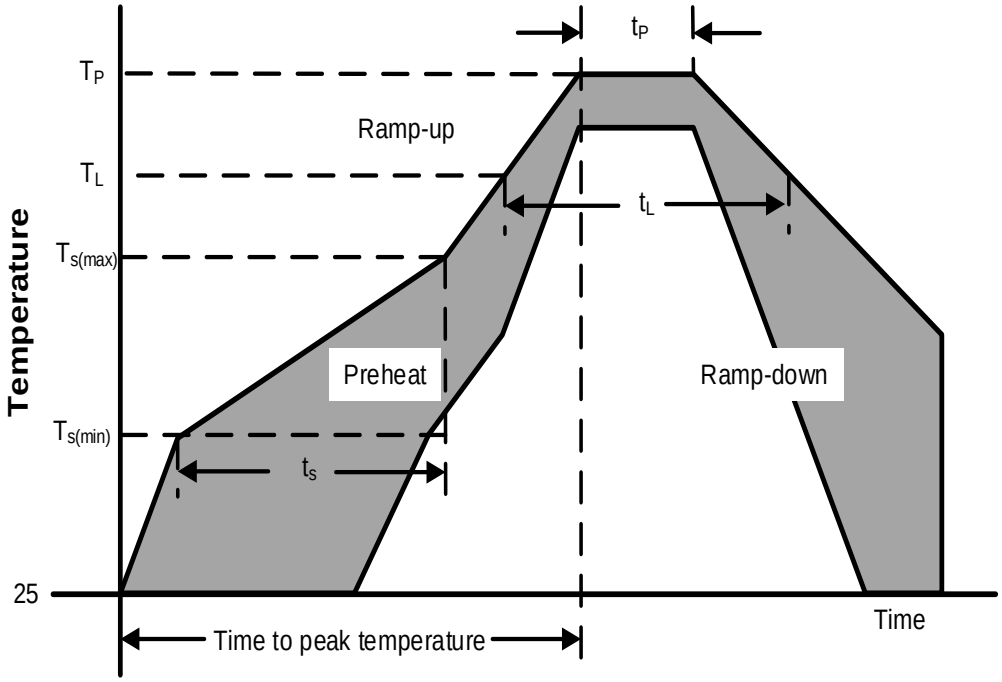


Figure 6. f_T vs. I_C



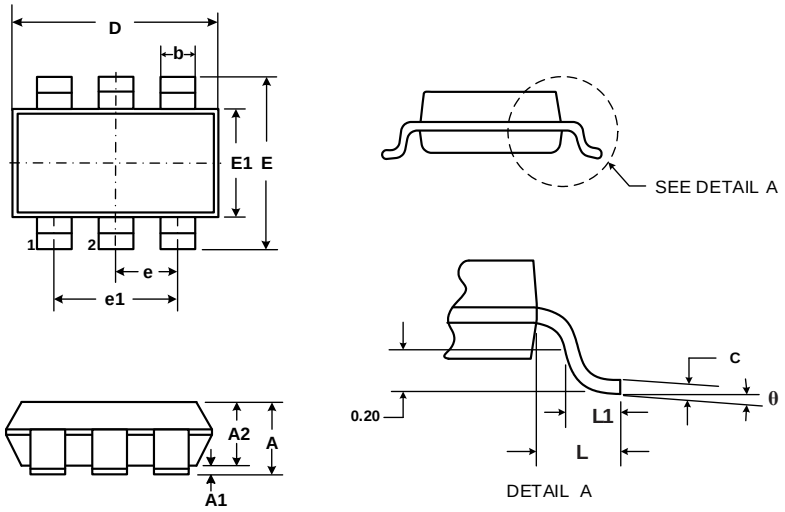
Soldering Parameters

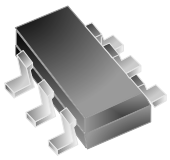
Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ($T_{s(min)}$)	150°C
	Temperature Max ($T_{s(max)}$)	200°C
	Time (min to max) (ts)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{S(max)}$ to T_L——Ramp-up Rate		5°C/second max
Reflow	Temperature (T_L) (Liquidus)	217°C
	Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_P)		260+0/-5 °C
Time within actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		280°C



Outline Drawing – SOT-363-6L

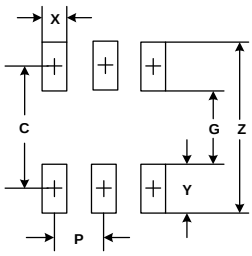
PACKAGE OUTLINE





SOT-363

DIMENSIONS				
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E1	1.150	1.350	0.045	0.053
E	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	``0°	8°

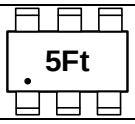


DIMENSIONS		
DIM	INCHES	MILLIMETERS
Z	0.110	2.79
G	0.043	1.09
C	0.076	1.94
P	0.026 TYP	0.65 TYP
X	0.016	0.40
Y	0.033	0.85

Notes:

Controlling Dimension: Millimeter.

Marking Codes

Part Number	WT856BDW
Marking Code	

Package Information

Qty：3k/Reel

CONTACT INFORMATION

No.1001, Shiwan (7) Road, Pudong District, Shanghai, P.R.China.201207
Tel: 86-21-68969993 Fax: 86-21-50757680 Email: market@way-on.com
WAYON website: **http://www.way-on.com**
For additional information, please contact your local Sales Representative.

WAYON ® is registered trademark of Wayon Corporation.

Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.